| L                | Hits   | Search Text   | DB    | Time stamp                       |
|------------------|--------|---|-------|----------------------------------|
| -                | 227    | 438/658.ccls.   | USPAT | 2004/04/20                       |
| -                | 137    | 438/658.ccls. and conductive  | ŲSPAT | 11:39<br>2003/11/18              |
| -                | 136    | 438/658.ccls. and conductive and layer  | USPAT | 10:36<br>  2003/11/18<br>  10:37 |
| * -              | . 68   | 438/658.ccls. and conductive and layer and via  | USPAT | 2003/11/18<br>10:37              |
| -                | 31     | 438/658.ccls. and conductive and layer and via and electromigration   | USPAT | 2003/11/18<br>10:37              |
| -                | . 5    | 438/658.ccls. and conductive and layer and via and electromigration and dopant  | USPAT | 2003/11/18<br>10:37              |
|                  | 1      | 438/658.ccls. and conductive and layer and via and electromigration and dopant  | USPAT | 2003/11/18<br>10:38              |
| -                | . 2    | and aluminum and concentrat\$4 and atomic 438/658.ccls. and conductive and layer and via and electromigration and dopant              | USPAT | 2003/11/18                       |
|                  | . 5    | and aluminum and concentrat\$4  |       | 12:27                            |
|                  | 3      | 438/658.ccls. and conductive and layer and via and electromigration and dopant and aluminum   | USPAT | 2003/11/24<br>11:49              |
| -                | 51     | 438/658.ccls. and "conductive layer"  | USPAT | 2003/11/21<br>14:11              |
| -                | 50     | 438/658.ccls. and "conductive layer" and substrate  | USPAT | 2003/11/21<br>14:11              |
| [ <del>-</del> , | . 21   | 438/658.ccls. and "conductive layer" and substrate and "dielectric layer"   | USPAT | 2003/11/21<br>14:11              |
| -                | 15<br> | 438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and   | USPAT | 2003/11/21<br>14:11              |
| _                | 12     | "barrier layer" 438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and   | USPAT | 2003/11/21<br>14:12              |
|                  | . 0    | "barrier layer" and via 438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and                                 | USPAT | 2003/11/21<br>14:12              |
| -                | . 6    | "barrier layer" and via and dopant<br>438/658.ccls. and "conductive layer" and<br>substrate and "dielectric layer" and                | USPAT | 2003/11/21 14:14                 |
| -                | 6      | "barrier layer" and via and dop\$4<br>438/658.ccls. and "conductive layer" and  | USPAT | 2003/11/21                       |
|                  |        | substrate and "dielectric layer" and "barrier layer" and via and dop\$4 and   |       | 14:15                            |
| -                | . 2    | electromigration 438/658.ccls. and "conductive layer" and substrate and "dielectric layer" and "barrier layer" and via and dop\$4 and | USPAT | 2003/11/21<br>15:19              |
| -                | 0      | electromigration and atomic 438/658.ccls. and "conductive layer" and  | USPAT | 2003/11/21                       |
|                  | . *    | substrate and "dielectric layer" and "barrier layer" and via and dop\$4 and electromigration and atomic and implant                   | *     | 15:19                            |
| -                | 2      | electromigration and atomic and implant 438/658.ccls. and conductive and layer and via and electromigration and dopant                | USPAT | 2003/11/24                       |
| _                | 2      | and via and electromigration and dopant and aluminum and ion 438/658.ccls. and conductive and layer                                   | USPAT | 11:49                            |
|                  | -      | and via and electromigration and dopant and aluminum and ion and gas  | JULAI | 11:50                            |
| -                | 4      | (("5614764") or ("5904560") or<br>("5909635") or ("6191029")).PN.   | USPAT | 2004/04/20<br>11:40              |
| <del>-</del>     | 3 .    | ((("5614764") or ("5904560") or ("5909635") or ("6191029")).PN.) and conduct\$4 and dielectric  | USPAT | 2004/04/20                       |
| -<br>            | 2      | ((("5614764") or ("5904560") or ("5909635") or ("6191029")).PN.) and  | USPAT | 2004/04/20                       |
| -                | . 0    | conduct\$4 and dielectric and via<br>((("5614764") or ("5904560") or<br>("5909635") or ("6191029")).PN.) and                          | USPAT | 2004/04/20                       |
|                  |        | conduct\$4 and dielectric and via and etch and ion  |       |                                  |

| ·   |     | ,      | 1 // / / / / / / / / / / / / / / / / /     |            |            |
|-----|-----|--------|--|------------|------------|
| -   | •   | 1      | ((("5614764") or ("5904560") or            | USPAT      | 2004/04/20 |
| ĺ   |     |        | ("5909635") or ("6191029")).PN.) and       |            | 14:16      |
|     | •   | 1      | conduct\$4 and dielectric and via and etch |            | ·          |
| -   |     | 0      | 438/658.                                   | USPAT      | 2004/04/20 |
| l ' |     |        |  |            | 14:16      |
| -   |     | 235    | 438/658.ccls.                              | USPAT      | 2004/04/20 |
|     |     |        |  |            | 14:17      |
| l – |     | 50     | 438/658.ccls. and substrate and conduct\$4 | USPAT      | 2004/04/20 |
|     |     |        | and dielectric and via                     | 051111     | 14:18      |
| _   |     | 35     |  | USPAT      | 2004/04/20 |
|     |     |        | and dielectric and via and tin             | USERI      |            |
| _   |     | 23     |  | IICD A III | 14:29      |
| 1   |     | 23     | conduct\$4 and dielectric and via and tin  | USPAT      | 2004/04/20 |
| i _ |     | . 3    | 438/658.ccls. and substrate with           |            | 15:03      |
| -   |     | )      | 430/658.CCIS. and substrate with           | USPAT      | 2004/04/29 |
| ,   |     |        | conduct\$4 with barrier and dielectric and |            | 10:18      |
|     |     | _      | via and tin                                |            |            |
| -   |     | 0      |  | USPAT      | 2004/04/21 |
| l · |     |        | and dielectric and via and tin             |            | 09:21      |
| -   |     | 418    | substrate with conduct\$4 with barrier and | USPAT      | 2004/04/21 |
|     |     |        | dielectric and via and tin                 |            | 09:43      |
| -   |     | 2      | substrate with conduct\$4 with barrier and | USPAT      | 2004/04/21 |
|     |     |        | dielectric and via and tin and             |            | 09:43      |
|     |     |        | electronmigration                          |            | 03.13      |
|     |     | 142    | substrate with conduct\$4 with barrier and | USPAT      | 2004/04/21 |
|     |     |        | dielectric and via and tin and             | OBIAI      | 09:44      |
|     |     |        | electromigration                           |            | 09:44      |
| _   |     | 95     | 438/658.ccls. and conduct\$4 with          | IICDAM     | 2004/04/20 |
|     |     | ) 5    | substrate                                  | USPAT      | 2004/04/29 |
|     | -   | 87     |  |            | 10:20      |
| 7   |     | 0 /    | 438/658.ccls. and conduct\$4 with          | USPAT      | 2004/04/29 |
|     |     | 4.0    | substrate and (dielectric or oxide)        |            | 10:21      |
|     |     | 49     |  | USPAT      | 2004/04/29 |
|     |     |        | substrate and (dielectric or oxide) and    |            | 10:21      |
|     |     |        | via  |            |            |
|     |     | 19     | 438/658.ccls. and conduct\$4 with          | USPAT      | 2004/04/29 |
|     | ٠.  |        | substrate and (dielectric or oxide) and    |            | 10:21      |
|     |     |        | via and (dopant or impur\$4)               |            | •          |
| _   |     | 10     | 438/658.ccls. and conduct\$4 with          | USPAT      | 2004/04/29 |
|     |     |        | substrate and (dielectric or oxide) and    |            | 10:22      |
|     |     |        | via and (dopant or impur\$4) and barrier   |            |            |
| _   |     | 1      | 438/658.ccls. and conduct\$4 with          | USPAT      | 2004/04/29 |
|     |     | _      | substrate and (dielectric or oxide) and    | OBIAI      | 10:22      |
|     |     |        | via and (dopant or impur\$4) and barrier   |            | 10.22      |
|     |     |        | and ion and implant\$4 and gas and trench  |            |            |
| _   |     | 2      | 438/658.ccls. and conduct\$4 with          | HODAM      | 2004/04/00 |
| _   |     |        |  | USPAT      | 2004/04/29 |
|     |     |        | substrate and (dielectric or oxide) and    |            | 10:34      |
|     |     | 0      | via and (dopant or impur\$4) and barrier   |            |            |
|     |     | ا ہے ا | and ion and implant\$4 and gas             |            |            |
| -   |     | 3      | 438/658.ccls. and conduct\$4 with          | USPAT ·    | 2004/04/29 |
|     |     |        | substrate and (dielectric or oxide) and    |            | 10:36      |
|     | · · |        | via and (dopant or impur\$4) and barrier   | •          | ,          |
|     |     |        | and ion and implant\$4                     |            |            |
| -   |     | 7      | 438/658.ccls. and conduct\$4 with          | USPAT      | 2004/04/29 |
|     |     |        | substrate and (dielectric or oxide) and    | ,          | 10:44      |
|     |     |        | via and (dopant or impur\$4) and barrier   |            |            |
|     | - 1 |        | and ion                                    |            |            |
|     | 1   |        |  |            | 0.00       |